



Product Summary

- $R_{DS(ON)}$, $V_{GS} @ -10V$, $I_D @ -3.0A < 95m\Omega$
- $R_{DS(ON)}$, $V_{GS} @ -4.5V$, $I_D @ -2.6A < 128m\Omega$

Application

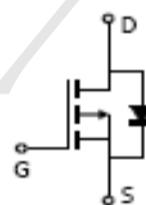
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

SOT-23



Circuit diagram



Marking:



Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V_{DS}	-40	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-3.0	A
Pulsed Drain Current ^(Note 4)	I_{DM}	-12.4	
Power Dissipation	$T_a=25^\circ C$	1.25	W
	Derate above $25^\circ C$	10	$mW/^\circ C$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55~150	$^\circ C$
Typical Thermal Resistance - Junction to Ambient ^(Note 3)	$R_{\theta JA}$	100	$^\circ C/W$



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AP2321GN-TP

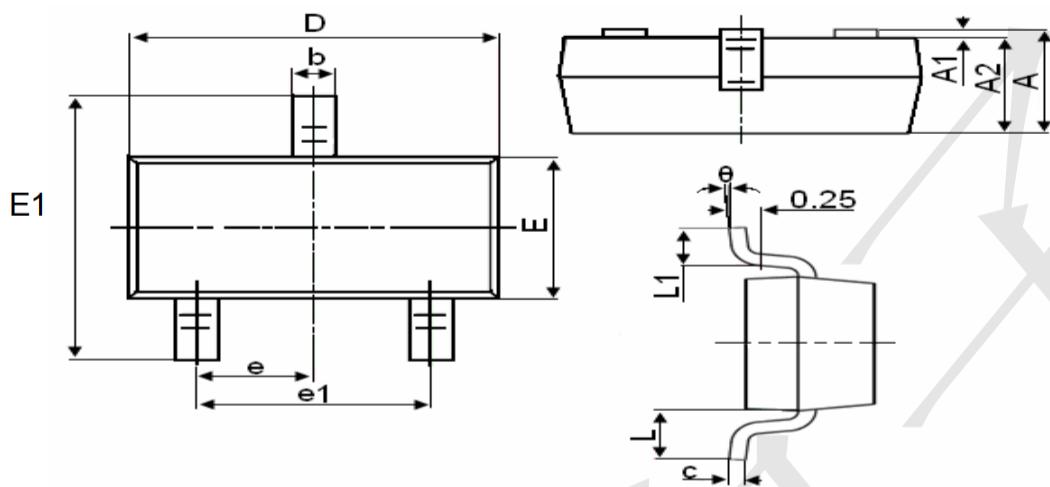
40V P-Channel Enhancement Mode MOSFET

www.sot23.com.tw

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-40	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	-1.5	-2.5	
Drain-Source On-State Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-3.1\text{A}$	-		95	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-1.2\text{A}$	-		128	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=-40\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Dynamic (Note 5)						
Total Gate Charge	Q_g	$V_{\text{DS}}=-20\text{V}, I_{\text{D}}=-3.1\text{A}, V_{\text{GS}}=-4.5\text{V}$ (Note 1,2)	-	6	-	nC
Gate-Source Charge	Q_{gs}		-	1.6	-	
Gate-Drain Charge	Q_{gd}		-	2.3	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=-20\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$	-	505	-	pF
Output Capacitance	C_{oss}		-	48	-	
Reverse Transfer Capacitance	C_{rss}		-	33	-	
Turn-On Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}}=-20\text{V}, I_{\text{D}}=-2.5\text{A}, V_{\text{GS}}=-10\text{V}, R_{\text{G}}=1\Omega$ (Note 1,2)	-	6	-	ns
Turn-On Rise Time	t_{r}		-	35	-	
Turn-Off Delay Time	$t_{\text{d}(\text{off})}$		-	18	-	
Turn-Off Fall Time	t_{f}		-	10	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_s	---	-	-	-1.0	A
Diode Forward Voltage	V_{SD}	$I_s=-1.0\text{A}, V_{\text{GS}}=0\text{V}$	-	-0.82	-1.2	V
Reverse Recovery Time	t_{rr}	$V_{\text{GS}}=0\text{V}, I_s=-2.5\text{A}$ $dI_F/dt=100\text{A}/\mu\text{s}$	-	13	-	ns
Reverse Recovery Charge	Q_{rr}		-	8.7	-	nC

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e		0.950TYP
e1	1.800	2.000
L		0.550REF
L1	0.300	0.500
θ	0°	8°